

L Number	Hits	Search Text	DB	Time stamp
-	14515	("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)	USPAT; US-PGPUB	2002/07/25 14:58
-	1285	((("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)) SAME trench	USPAT; US-PGPUB	2002/07/25 12:36
-	280	((("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)) SAME trench) SAME nitride SAME (photoresist or resist or mask)	USPAT; US-PGPUB	2002/07/25 17:16
-	147	((("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)) WITH (planar\$))	USPAT; US-PGPUB	2002/07/25 15:25
-	191	((("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)) WITH (planar\$))	USPAT; US-PGPUB	2002/07/25 15:26
-	143	((("wet etching" or "wet etch" or "isotropic etch" or "isotropic etching" or HF or "hydrofluoric") WITH (oxide or dioxide)) WITH (planar\$)) and (trench or isolation)	USPAT; US-PGPUB	2002/07/25 17:16